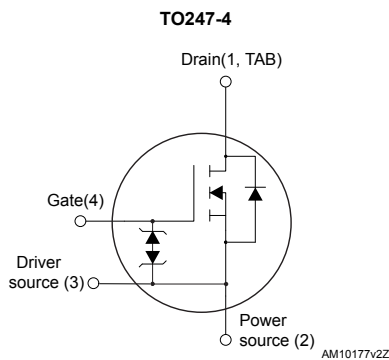
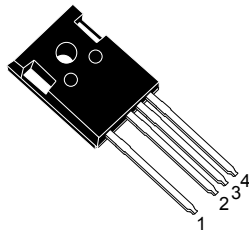


# N-channel 600 V, 32 mΩ typ., 72 A, MDmesh™ M6 Power MOSFET in a TO247-4 package



### Product status link

[STW75N60M6-4](#)

### Product summary

Order code	STW75N60M6-4
Marking	75N60M6
Package	TO247-4
Packing	Tube

## Features

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>
STW75N60M6-4	600 V	36 mΩ	72 A

- Reduced switching losses
- Lower R<sub>DS(on)</sub> per area vs previous generation
- Low gate input resistance
- 100% avalanche tested
- Zener-protected
- Excellent switching performance thanks to the extra driving source pin

## Applications

- Switching applications
- LLC converters
- Boost PFC converters

## Description

The new MDmesh™ M6 technology incorporates the most recent advancements to the well-known and consolidated MDmesh family of SJ MOSFETs. STMicroelectronics builds on the previous generation of MDmesh devices through its new M6 technology, which combines excellent R<sub>DS(on)</sub> per area improvement with one of the most effective switching behaviors available, as well as a user-friendly experience for maximum end-application efficiency.

# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate-source voltage	$\pm 25$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	72	A
	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	45	A
$I_{DM}^{(1)}$	Drain current (pulsed)	288	A
$P_{TOT}$	Total power dissipation at $T_C = 25\text{ }^\circ\text{C}$	446	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(3)}$	MOSFET $dv/dt$ ruggedness	100	
$T_{stg}$	Storage temperature range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating junction temperature range		

1. Pulse width is limited by safe operating area.
2.  $I_{SD} \leq 72\text{ A}$ ,  $di/dt = 400\text{ A}/\mu\text{s}$ ,  $V_{DS(peak)} < V_{(BR)DSS}$ ,  $V_{DD} = 400\text{ V}$
3.  $V_{DS} \leq 480\text{ V}$

**Table 2. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	0.28	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient	50	$^\circ\text{C}/\text{W}$

**Table 3. Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not repetitive (pulse width limited by $T_{Jmax}$ )	11	A
$E_{AS}$	Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	1.4	J

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 4. On/off-states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$ , $I_D = 1\text{ mA}$	600			V
$I_{DSS}$	Zero-gate voltage drain current	$V_{GS} = 0\text{ V}$ , $V_{DS} = 600\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$ , $V_{DS} = 600\text{ V}$ , $T_C = 125\text{ °C}^{(1)}$			100	
$I_{GSS}$	Gate-body leakage current	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 25\text{ V}$			$\pm 5$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	3.25	4	4.75	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 36\text{ A}$		32	36	m $\Omega$

1. Defined by design, not subject to production test.

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{GS} = 0\text{ V}$ , $V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$	-	4850	-	pF
$C_{oss}$	Output capacitance		-	380	-	pF
$C_{riss}$	Reverse transfer capacitance		-	3.5	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{GS} = 0\text{ V}$ , $V_{DS} = 0\text{ to }480\text{ V}$	-	851	-	pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	1.5	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 480\text{ V}$ , $I_D = 72\text{ A}$ , $V_{GS} = 0\text{ to }10\text{ V}$ (see Figure 2)	-	106	-	nC
$Q_{gs}$	Gate-source charge		-	32	-	nC
$Q_{gd}$	Gate-drain charge		-	45	-	nC

1.  $C_{oss\text{ eq.}}$  is defined as the constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$ .

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$ , $I_D = 36\text{ A}$ , $R_G = 4.7\text{ }\Omega$ , $V_{GS} = 10\text{ V}$ (see Figure 1 and Figure 6)	-	TBD	-	ns
$t_r$	Rise time		-	TBD	-	ns
$t_{d(off)}$	Turn-off delay time		-	TBD	-	ns
$t_f$	Fall time		-	TBD	-	ns

**Table 7. Source-drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		72	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		288	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0\text{ V}$ , $I_{SD} = 72\text{ A}$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 72\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ (see Figure 3)	-	367		ns
$Q_{rr}$	Reverse recovery charge		-	6.4		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	35		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 72\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ , $T_J = 150\text{ }^\circ\text{C}$ (see Figure 3)	-	552		ns
$Q_{rr}$	Reverse recovery charge		-	13.7		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	49.6		A

1. Pulse width is limited by safe operating area.
2. Pulse test: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%.

## 2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

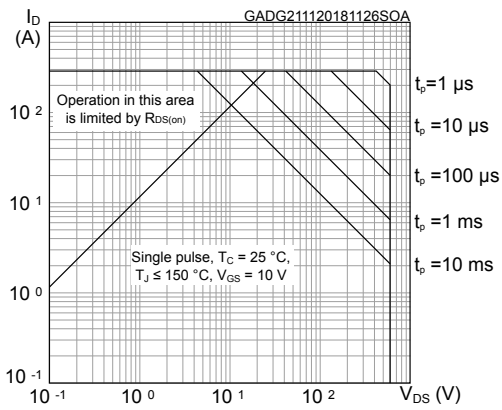


Figure 2. Thermal impedance

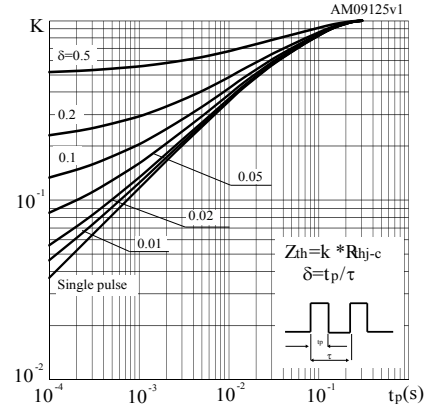


Figure 3. Output characteristics

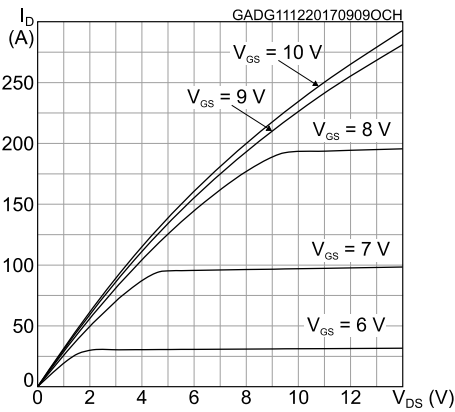


Figure 4. Transfer characteristics

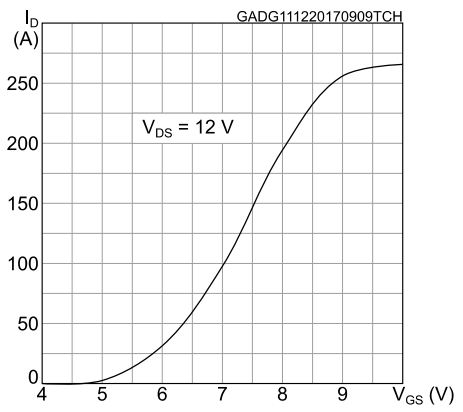


Figure 5. Gate charge vs gate-source voltage

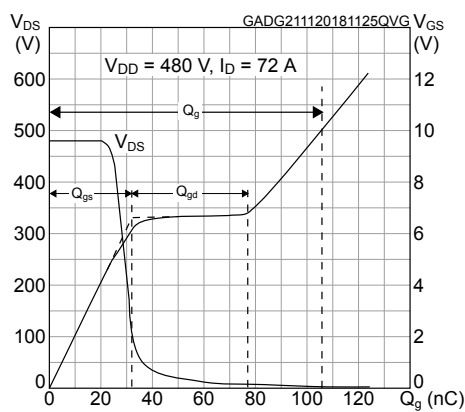


Figure 6. Static drain-source on-resistance

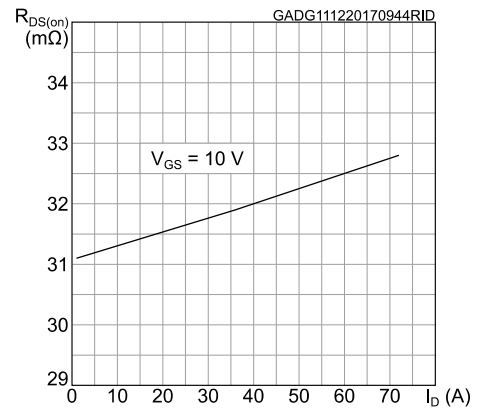


Figure 7. Normalized on-resistance vs temperature

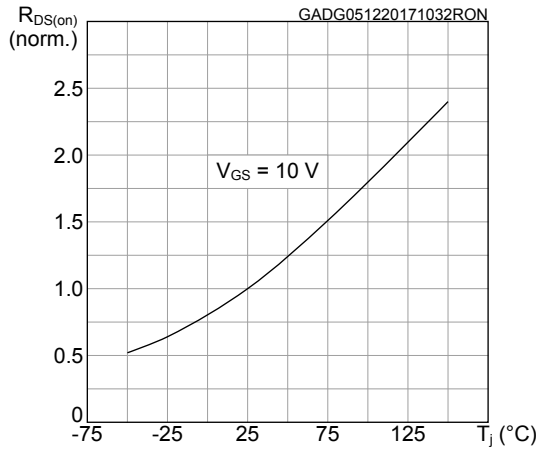


Figure 8. Normalized  $V_{(BR)DSS}$  vs temperature

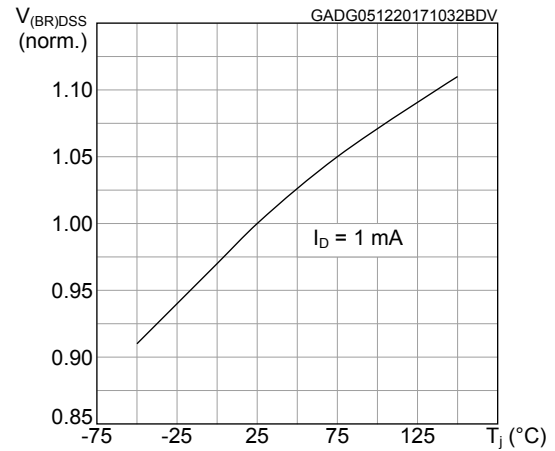


Figure 9. Capacitance variations

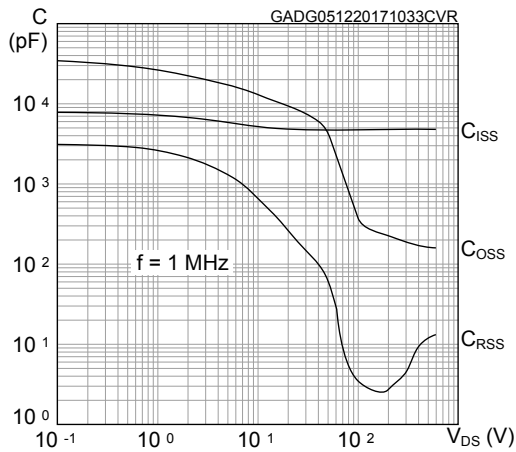


Figure 10. Normalized gate threshold voltage vs temperature

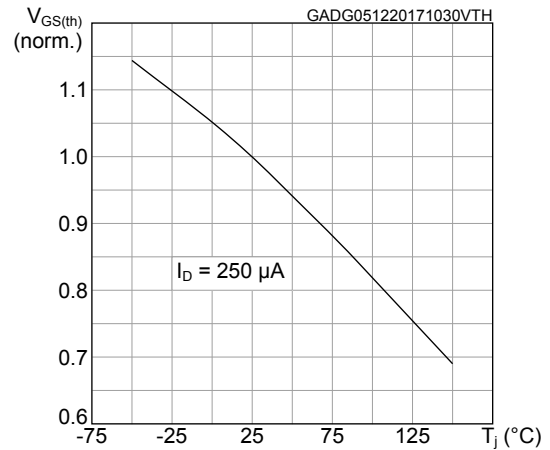


Figure 11. Output capacitance stored energy

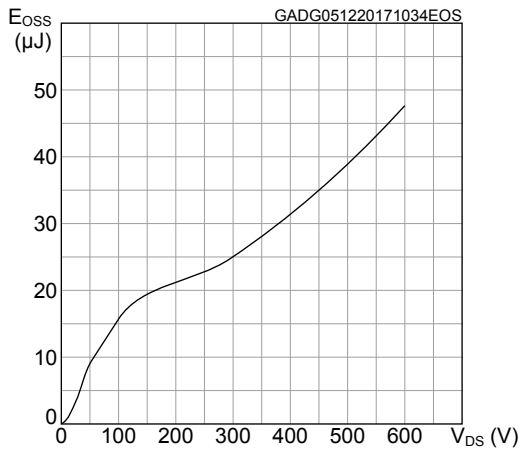
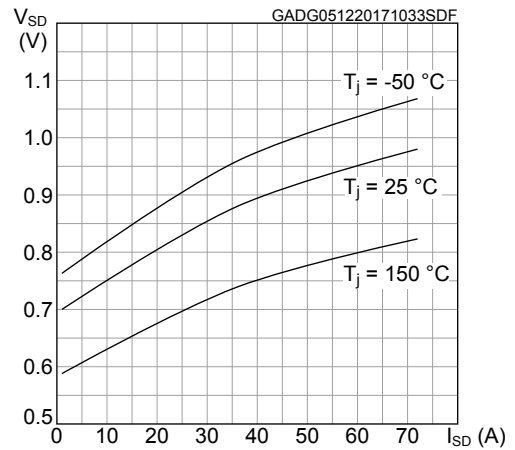
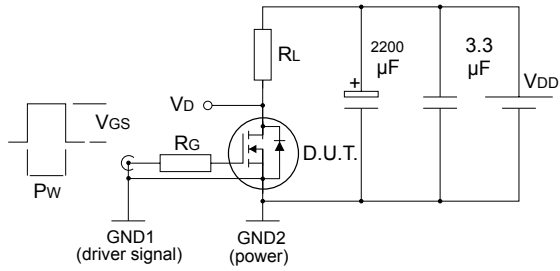


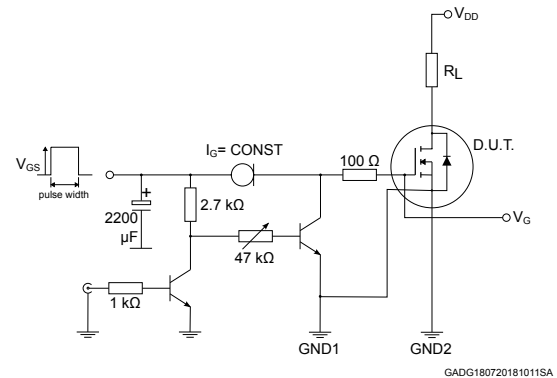
Figure 12. Source-drain diode forward characteristics



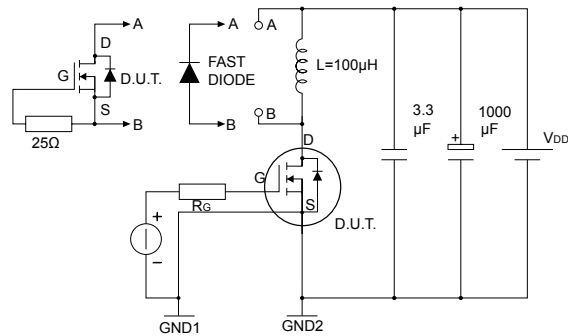
### 3 Test circuits

**Figure 13. Switching times test circuit for resistive load**


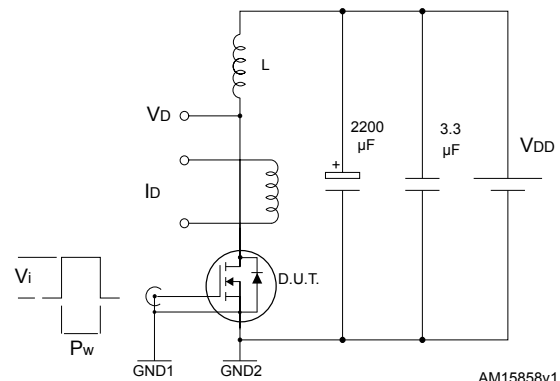
AM15855v1

**Figure 14. Test circuit for gate charge behavior**


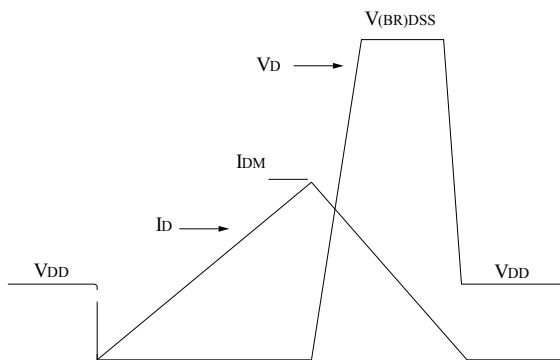
GADG180720181011SA

**Figure 15. Test circuit for inductive load switching and diode recovery times**


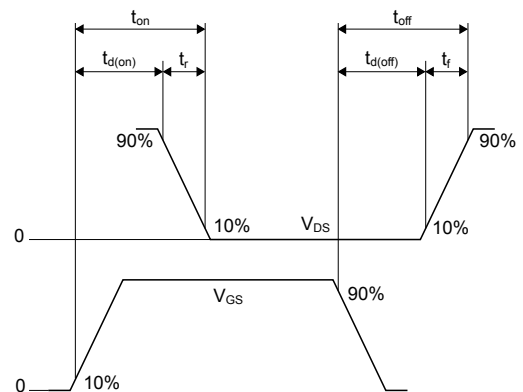
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**Figure 16. Unclamped inductive load test circuit**


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**Figure 17. Unclamped inductive waveform**


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**Figure 18. Switching time waveform**


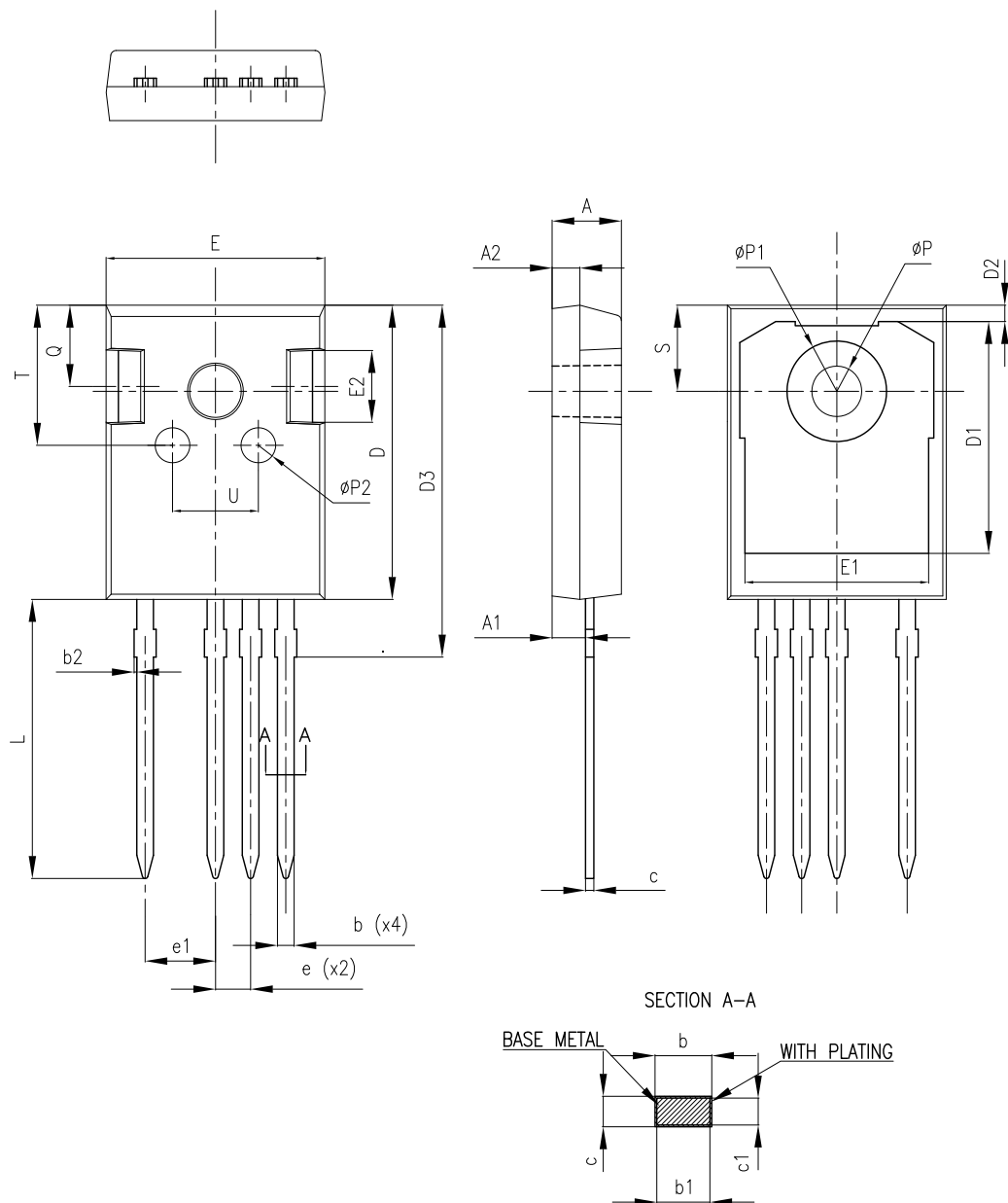
AM01473v1

## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK®** packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

### 4.1 TO247-4 package information

Figure 19. TO247-4 package outline



8405626\_2



**Table 8. TO247-4 mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
b	1.16		1.29
b1	1.15	1.20	1.25
b2	0		0.20
c	0.59		0.66
c1	0.58	0.60	0.62
D	20.90	21.00	21.10
D1	16.25	16.55	16.85
D2	1.05	1.20	1.35
D3	24.97	25.12	25.27
E	15.70	15.80	15.90
E1	13.10	13.30	13.50
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
e	2.44	2.54	2.64
e1	4.98	5.08	5.18
L	19.80	19.92	20.10
P	3.50	3.60	3.70
P1			7.40
P2	2.40	2.50	2.60
Q	5.60		6.00
S		6.15	
T	9.80		10.20
U	6.00		6.40

## Revision history

**Table 9. Document revision history**

Date	Revision	Changes
11-Dec-2017	1	Initial version
07-Dec-2018	2	Removed maturity status indication from cover page. The document status is production data. Updated schematic diagram on cover page. Updated <a href="#">Table 1. Absolute maximum ratings</a> , <a href="#">Table 5. Dynamic</a> and <a href="#">Table 7. Source-drain diode</a> . Updated <a href="#">Section 2.1 Electrical characteristics (curves)</a> . Minor text changes

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